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## U.S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

[illegible]

## OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
		"A Precise On-Chip Voltage Generator for a Gigascale DRAM with a Negative Word-Line Scheme", by Tanaka et al., IEEE Journal of Solid-State Circuits, Vol. 34, No. 8, 8/1999, pp. 1084-1090.
		"Ultra LSI Memory" by Kiyoo Ito, Advanced Electronics Series, November 5, 1994, published by Baifukan, pp. 351-371.
		"An Experimental 256-Mb DRAM with Boosted Sense-Ground Scheme", by Asakura et al., IEEE Journal of Solid-State Circuits, Vol. 29, No. 11, 11/1994, pp. 1303-1309.

**EXAMINER**

DATE CONSIDERED

\*EXAMINER: Initial if reference considered whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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